

Noor Azrina Talik

List of Publications by Year in descending order

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840776

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42
docs citations

42
times ranked

426
citing authors

#	ARTICLE	IF	CITATIONS
1	Improved performance of InGaN/GaN LED by optimizing the properties of the bulk and interface of ITO on p-GaN. Applied Surface Science, 2021, 540, 148406.	6.1	5
2	The effect of Multi Quantum Well growth regime transition on MQW/p-GaN structure and light emitting diode (LED) performance. Materials Science in Semiconductor Processing, 2021, 121, 105431.	4.0	5
3	The crystallographic quality and band-edge transition of as-deposited PALE AlN films via metal organic chemical vapor deposition. Journal of Materials Science: Materials in Electronics, 2021, 32, 3211-3221.	2.2	2
4	Diminishing the Induced Strain and Oxygen Incorporation on Aluminium Nitride Films Deposited Using Pulsed Atomic-Layer Epitaxy Techniques at Standard Pressure MOCVD. Journal of Electronic Materials, 2021, 50, 2313-2322.	2.2	5
5	Fabrication of DNA/NiSi NWs and Ag NPs-NiSi NWs-based Schottky diodes for DNA detection with fast response time. Journal of Materials Science: Materials in Electronics, 2021, 32, 7889-7905.	2.2	3
6	Impact of sandwiched strain periodic multilayer AlN/GaN on strain and crystalline quality of a-plane GaN. Scientific Reports, 2021, 11, 9724.	3.3	3
7	Exploration of 2D Ti3C2 MXene for all solution processed piezoelectric nanogenerator applications. Scientific Reports, 2021, 11, 17432.	3.3	14
8	Effect of silver nanoparticles deposited on indium tin oxide by plasma-assisted hot-filament evaporation on phosphorescent organic light-emitting diode performance. Applied Surface Science, 2021, 570, 151280.	6.1	2
9	Electronic surface, optical and electrical properties of p-type GaN activated via in-situ MOCVD and ex-situ thermal annealing in InGaN/GaN LED. Materials Science in Semiconductor Processing, 2020, 106, 104757.	4.0	0
10	Positioning of periodic AlN/GaN multilayers: Effect on crystalline quality of a-plane GaN. Materials Science in Semiconductor Processing, 2020, 105, 104700.	4.0	15
11	Improvement of MAPbI3 perovskite blend with TiO2 nanoparticles as ReRAM device. Ceramics International, 2020, 46, 29041-29051.	4.8	10
12	Agglomeration enhancement of AlN surface diffusion fluxes on a (0 0 0 1)-sapphire substrate grown by pulsed atomic-layer epitaxy techniques via MOCVD. CrystEngComm, 2020, 22, 3309-3321.	2.6	7
13	Surface plasmon resonance of silver nano-dendrites improved light absorption in an organic photovoltaic active layer. Micro and Nano Letters, 2020, 15, 866-871.	1.3	3
14	Influence of different morphology of carbon nanostructures on the structural and optical properties of decorated single crystalline hematite nanocubes for photoelectrochemical applications. Applied Surface Science, 2019, 498, 143845.	6.1	6
15	Effects of pulse cycle number on the quality of pulsed atomic-layer epitaxy AlN films grown via metal organic chemical vapor deposition. Japanese Journal of Applied Physics, 2019, 58, SC1037.	1.5	8
16	In-situ tuning of Sn doped In2O3 (ITO) films properties by controlling deposition Argon/Oxygen flow. Applied Surface Science, 2019, 479, 1220-1225.	6.1	17
17	Ammonia flux tailoring on the quality of AlN epilayers grown by pulsed atomic-layer epitaxy techniques on (0 0 0 1)-oriented sapphire substrates via MOCVD. CrystEngComm, 2019, 21, 2009-2017.	2.6	21
18	Multiple resistive switching behaviours of CH3NH3PbI3 perovskite film with different metal electrodes. Applied Surface Science, 2019, 473, 194-202.	6.1	22

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19	Prospects of Low-Cost Photometers for Colorimetric Serum Iron Concentration Determination. IFMBE Proceedings, 2018, , 165-169.	0.3	0
20	Energy level alignment of blended organic semiconductors and electrodes at the interface. Current Applied Physics, 2018, 18, 982-992.	2.4	5
21	Potential Point-of-Care Microfluidic Devices to Diagnose Iron Deficiency Anemia. Sensors, 2018, 18, 2625.	3.8	10
22	Tailoring electronics structure, electrical and magnetic properties of synthesized transition metal (Ni)-doped ZnO thin film. Journal of Alloys and Compounds, 2018, 769, 640-648.	5.5	18
23	Ultraviolet Laser Diode Ablation Process for CMOS 45 nm Copper Low-K Semiconductor Wafer. Procedia Engineering, 2017, 184, 360-369.	1.2	6
24	In-situ analysis energy level alignment at solution processed HAT(CN) 6 /PVK (PVK:TAPC) interface via XPS and UPS. Current Applied Physics, 2017, 17, 1094-1099.	2.4	7
25	Review on recent Developments on Fabrication Techniques of Distributed Feedback (DFB) Based Organic Lasers. Journal of Physics: Conference Series, 2017, 914, 012032.	0.4	3
26	Proton exchange membrane (PEM) and solid oxide (SOFC) fuel cell based vehicles-a review. , 2017, , .		9
27	Iron deficiency anaemia: with the conclusion of a need for iron reader. Journal of Physics: Conference Series, 2017, 914, 012028.	0.4	0
28	High efficiency solution processable organic light emitting diode through materials and interfacial engineering. , 2016, , .		0
29	Effect of mixed hole transporting host on the mobility, Gaussian density of states and efficiencies of a heterojunction phosphorescent organic light emitting diode. Journal Physics D: Applied Physics, 2016, 49, 155103.	2.8	7
30	Electrostatic model of the energy-bending within organic semiconductors: experiment and simulation. Journal of Physics Condensed Matter, 2016, 28, 365002.	1.8	8
31	Investigation into the Gaussian density of states widths of organic semiconductors. Journal Physics D: Applied Physics, 2016, 49, 325106.	2.8	14
32	Highly efficient processable molybdenum trioxide as a hole blocking interlayer for super-yellow organic light emitting diode. Journal Physics D: Applied Physics, 2016, 49, 395105.	2.8	3
33	Investigations of solution-processed charge generation unit with low concentration of small molecule doped in p-type/HAT-CN 6 for tandem OLED. Journal of Luminescence, 2016, 169, 61-64.	3.1	8
34	High efficiency solution processed fluorescent yellow organic light-emitting diode through fluorinated alcohol treatment at the emissive layer/cathode interface. Journal Physics D: Applied Physics, 2014, 47, 015106.	2.8	9
35	The efficiency enhancement of single-layer solution-processed blue phosphorescent organic light emitting diodes by hole injection layer modification. Journal Physics D: Applied Physics, 2014, 47, 205103.	2.8	14
36	Determination of energy levels at the interface between O ₂ plasma treated ITO/P3HT/PCBM and PEDOT:PSS/P3HT/PCBM using angular-resolved x-ray and ultraviolet photoelectron spectroscopy. Journal Physics D: Applied Physics, 2014, 47, 055109.	2.8	15

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37	Efficient green phosphorescent tandem organic light emitting diodes with solution processable mixed hosts charge generating layer. Journal of Luminescence, 2014, 154, 345-349.	3.1	11
38	Enhancement of the work function of indium tin oxide by surface modification using caesium fluoride. Journal Physics D: Applied Physics, 2013, 46, 475102.	2.8	15
39	Ionic contaminations level and cleaning flip chip BGA package via a new cleaning solvent technology. Microelectronics International, 2013, 30, 99-103.	0.6	0
40	Finite element analysis of thermal distributions of solder ball in flip chip ball grid array using ABAQUS. Microelectronics International, 2013, 30, 14-18.	0.6	8
41	Comparison Study on Shear Strength and Intermetallic Compound for SAC and Polymer Core Solder Balls. Advanced Science Letters, 2013, 19, 766-769.	0.2	0